

TinyLogic ULP-A Triple Buffer

NC7NP34

The NC7NP34 is a triple buffer in tiny footprint packages. The device is designed to operate for V_{CC} = 0.9 V to 3.6 V.

Features

- Designed for 0.9 V to 3.6 V V_{CC} Operation
- 2.7 ns t_{PD} at 3.3 V (Typ)
- Inputs/Outputs Over-Voltage Tolerant up to 3.6 V
- I_{OFF} Supports Partial Power Down Protection
- Source/Sink 2.6 mA at 3.3 V
- Available in US8 and MicroPak™ Packages
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

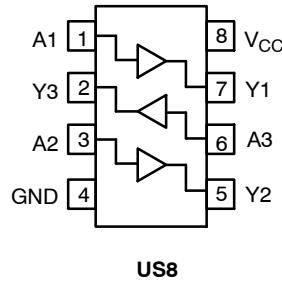


Figure 1. Pinout Diagrams (Top Views)

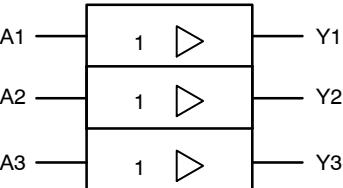
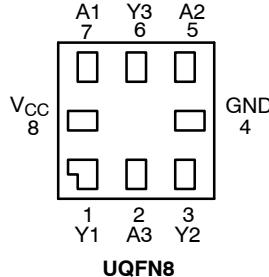


Figure 2. Logic Symbol

PIN ASSIGNMENT

Pin	US8	UQFN8
1	A1	Y1
2	Y3	A3
3	A2	Y2
4	GND	GND
5	Y2	A2
6	A3	Y3
7	Y1	A1
8	V_{CC}	V_{CC}

FUNCTION TABLE

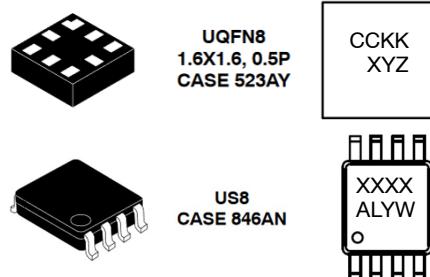
A Input	Y Output
L	L
H	H



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MARKING DIAGRAMS



CC,XXX = Specific Device Code
KK = 2-Digit Date Code Traceability Code
XY = 2-Digit Date Code Format
Z = Assembly Plant Code
A = Assembly Site
L = Wafer Lot Number
YW = Assembly Start Week

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 6 of this data sheet.

MAXIMUM RATINGS

Symbol	Characteristics	Value	Unit
V_{CC}	DC Supply Voltage	-0.5 to +4.3	V
V_{IN}	DC Input Voltage	-0.5 to +4.3	V
V_{OUT}	DC Output Voltage Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode ($V_{CC} = 0$ V)	-0.5 to $V_{CC} + 0.5$ -0.5 to +4.3 -0.5 to +4.3	V
I_{IK}	DC Input Diode Current $V_{IN} < GND$	-50	mA
I_{OK}	DC Output Diode Current $V_{OUT} < GND$	-50	mA
I_{OUT}	DC Output Source/Sink Current	± 50	mA
I_{CC} or I_{GND}	DC Supply Current per Supply Pin or Ground Pin	± 50	mA
T_{STG}	Storage Temperature Range	-65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
T_J	Junction Temperature Under Bias	+150	°C
θ_{JA}	Thermal Resistance (Note 2) US8 MicroPak	250 210	°C/W
P_D	Power Dissipation in Still Air US8 MicroPak	500 595	mW
MSL	Moisture Sensitivity	Level 1	-
F_R	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V_{ESD}	ESD Withstand Voltage (Note 3) Human Body Model Charged Device Model	2000 1000	V
$I_{Latchup}$	Latchup Performance (Note 4)	± 100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.
2. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow per JESD51-7.
3. HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.
4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	Positive DC Supply Voltage	0.9	3.6	V
V_{IN}	DC Input Voltage	0	3.6	V
V_{OUT}	DC Output Voltage Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode ($V_{CC} = 0$ V)	0 0 0	V_{CC} 3.6 3.6	
T_A	Operating Temperature Range	-40	+85	°C
t_r, t_f	Input Transition Rise and Fall Time $V_{CC} = 3.3$ V ± 0.3 V	0	10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			T _A = -40°C to +85°C		Unit
				Min	Typ	Max	Min	Max	
V _{IH}	High-Level Input Voltage		0.9	–	0.5	–	–	–	V
			1.1 to 1.3	0.65 x V _{CC}	–	–	0.65 x V _{CC}	–	
			1.4 to 1.6	0.65 x V _{CC}	–	–	0.65 x V _{CC}	–	
			1.65 to 1.95	0.65 x V _{CC}	–	–	0.65 x V _{CC}	–	
			2.3 to 2.7	1.6	–	–	1.6	–	
			3.0 to 3.6	2.1	–	–	2.1	–	
V _{IL}	Low-Level Input Voltage		0.9	–	0.5	–	–	–	V
			1.1 to 1.3	–	–	0.35 x V _{CC}	–	0.35 x V _{CC}	
			1.4 to 1.6	–	–	0.35 x V _{CC}	–	0.35 x V _{CC}	
			1.65 to 1.95	–	–	0.35 x V _{CC}	–	0.35 x V _{CC}	
			2.3 to 2.7	–	–	0.7	–	0.7	
			3.0 to 3.6	–	–	0.9	–	0.9	
V _{OH}	High-Level Output Voltage	V _{IN} = V _{IH} or V _{IL}							V
		I _{OH} = -20 µA	0.9	–	V _{CC} - 0.1	–	–	–	
			1.1 to 1.3	V _{CC} - 0.1	–	–	V _{CC} - 0.1	–	
			1.4 to 1.6	V _{CC} - 0.1	–	–	V _{CC} - 0.1	–	
			1.65 to 1.95	V _{CC} - 0.1	–	–	V _{CC} - 0.1	–	
			2.3 to 2.7	V _{CC} - 0.1	–	–	V _{CC} - 0.1	–	
			3.0 to 3.6	V _{CC} - 0.1	–	–	V _{CC} - 0.1	–	
		I _{OH} = -0.5 mA	1.1 to 1.3	0.75 x V _{CC}	–	–	0.70 x V _{CC}	–	
			1.4 to 1.6	1.07	–	–	0.99	–	
			1.65 to 1.95	1.24	–	–	1.22	–	
			2.3 to 2.7	1.95	–	–	1.87	–	
			3.0 to 3.6	2.61	–	–	2.55	–	
V _{OL}	Low-Level Output Voltage	V _{IN} = V _{IH} or V _{IL}							V
		I _{OL} = 20 µA	0.9	–	0.1	–	–	–	
			1.1 to 1.3	–	–	0.1	–	0.1	
			1.4 to 1.6	–	–	0.1	–	0.1	
			1.65 to 1.95	–	–	0.1	–	0.1	
			2.3 to 2.7	–	–	0.1	–	0.1	
			3.0 to 3.6	–	–	0.1	–	0.1	
		I _{OL} = 0.5 mA	1.1 to 1.3	–	–	0.3 x V _{CC}	–	0.3 x V _{CC}	
			1.4 to 1.6	–	–	0.31	–	0.37	
			1.65 to 1.95	–	–	0.31	–	0.35	
			2.3 to 2.7	–	–	0.31	–	0.33	
		I _{OL} = 1.5 mA	3.0 to 3.6	–	–	0.31	–	0.33	
		I _{OL} = 2.1 mA	3.0 to 3.6	–	–	0.31	–	0.33	
		I _{OL} = 2.6 mA	3.0 to 3.6	–	–	0.31	–	0.33	
I _{IN}	Input Leakage Current	V _{IN} = 0 V to 3.6 V	0.9 to 3.6	–	–	±0.1	–	±0.5	µA
I _{OFF}	Power Off Leakage Current	V _{IN} = 0 V to 3.6 V or V _{OUT} = 0 V to 3.6 V	0	–	–	0.5	–	0.5	µA
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	0.9 to 3.6	–	–	0.9	–	0.9	µA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

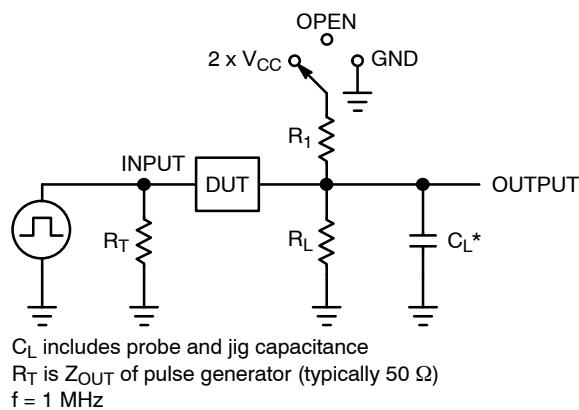
AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			T _A = -40°C to +85°C		Unit
				Min	Typ	Max	Min	Max	
t _{PLH} , t _{PHL}	Propagation Delay, A to Y (Figures 3 and 4)	R _L = 1 MΩ, C _L = 10 pF	0.9	—	45.0	—	—	—	ns
			1.10 to 1.30	—	11.9	25.9	—	34.3	
			1.40 to 1.60	—	6.2	14.8	—	15.0	
			1.65 to 1.95	—	4.4	12.0	—	12.2	
			2.3 to 2.7	—	3.3	9.4	—	9.9	
			3.0 to 3.6	—	2.7	8.3	—	9.0	
t _{PLH} , t _{PHL}	Propagation Delay, A to Y (Figures 3 and 4)	R _L = 1 MΩ, C _L = 15 pF	0.9	—	46.6	—	—	—	ns
			1.10 to 1.30	—	12.5	27.3	—	37.3	
			1.40 to 1.60	—	6.7	15.5	—	16.5	
			1.65 to 1.95	—	4.8	12.6	—	13.6	
			2.3 to 2.7	—	3.5	9.9	—	10.8	
			3.0 to 3.6	—	2.9	8.7	—	9.5	
t _{PLH} , t _{PHL}	Propagation Delay, A to Y (Figures 3 and 4)	R _L = 1 MΩ, C _L = 30 pF	0.9	—	51.3	—	—	—	ns
			1.10 to 1.30	—	14.5	31.6	—	46.3	
			1.40 to 1.60	—	8.2	17.8	—	18.2	
			1.65 to 1.95	—	5.9	14.4	—	15.9	
			2.3 to 2.7	—	4.2	11.3	—	12.8	
			3.0 to 3.6	—	3.4	9.2	—	10.7	

CAPACITIVE CHARACTERISTICS

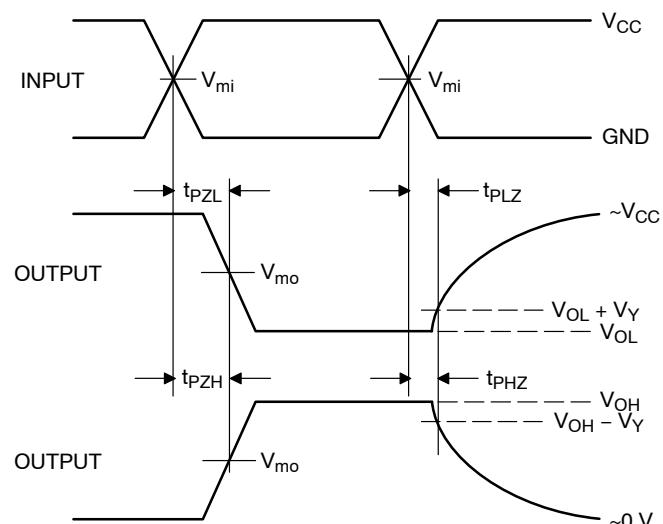
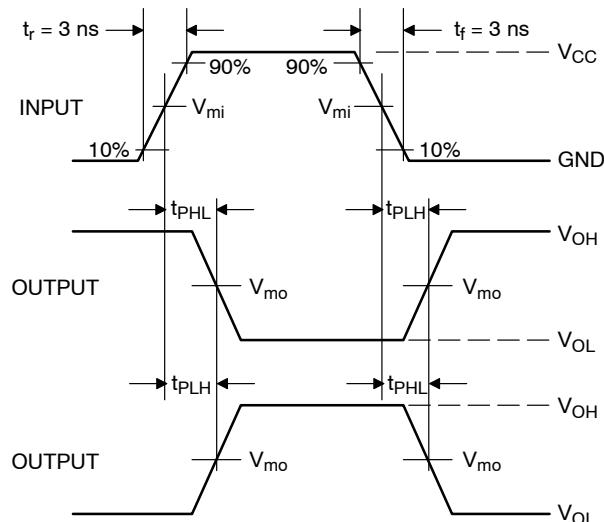
Symbol	Parameter	Test Condition	Typical (T _A = 25°C)	Unit
C _{IN}	Input Capacitance	V _{CC} = 0 V	2.0	pF
C _{OUT}	Output Capacitance	V _{CC} = 0 V	4.0	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	f = 10 MHz, V _{CC} = 0.9 to 3.6 V, V _{IN} = 0 V or V _{CC}	6.0	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption: P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.



Test	Switch Position
t_{PLH} / t_{PHL}	Open
t_{PLZ} / t_{PZL}	$2 \times V_{CC}$
t_{PHZ} / t_{PZH}	GND

Figure 3. Test Circuit



V_{CC}, V	V_{mi}, V	V_{mo}, V	V_Y, V
0.9	$V_{CC} / 2$	$V_{CC} / 2$	0.1
1.1 to 1.3	$V_{CC} / 2$	$V_{CC} / 2$	0.1
1.4 to 1.6	$V_{CC} / 2$	$V_{CC} / 2$	0.1
1.65 to 1.95	$V_{CC} / 2$	$V_{CC} / 2$	0.15
2.3 to 2.7	$V_{CC} / 2$	$V_{CC} / 2$	0.15
3.0 to 3.6	1.5	1.5	0.3

Figure 4. Switching Waveforms

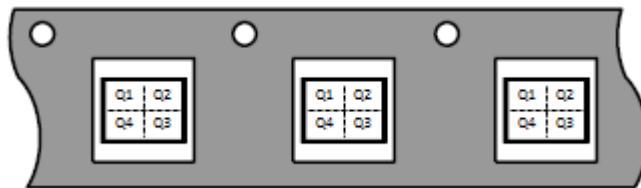
ORDERING INFORMATION

Device	Package	Marking	Pin 1 Orientation (See below)	Shipping [†]
NC7NP34K8X	US8	NP34	Q4	3000 / Tape & Reel
NC7NP34L8X	MicroPak, UQFN8	X7	Q4	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Pin 1 Orientation in Tape and Reel

Direction of Feed



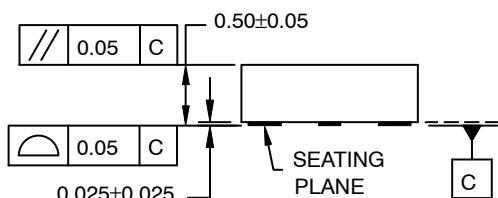
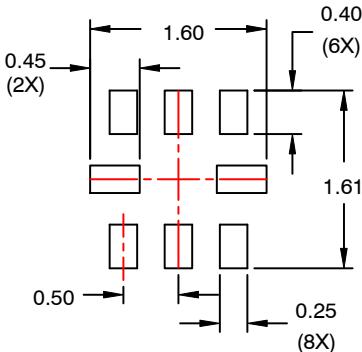
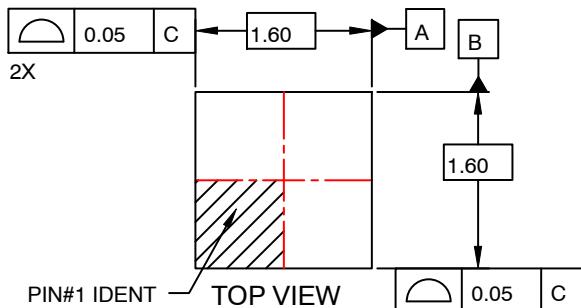
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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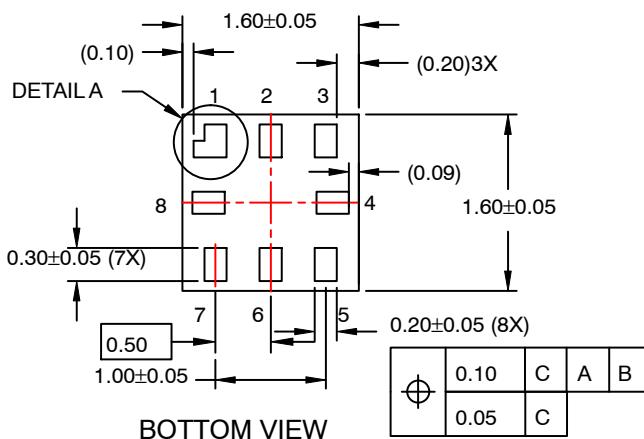
ON

**UQFN8 1.6X1.6, 0.5P
CASE 523AY
ISSUE O**

DATE 31 AUG 2016



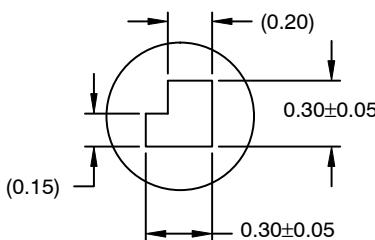
SIDE VIEW



RECOMMENDED LAND PATTERN

NOTES:

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- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
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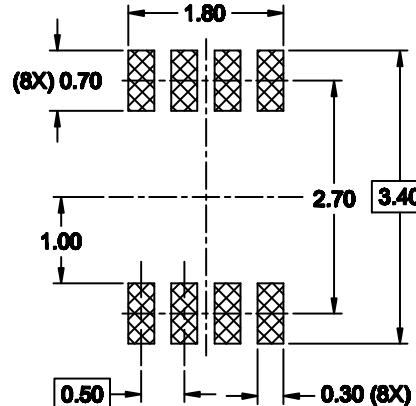
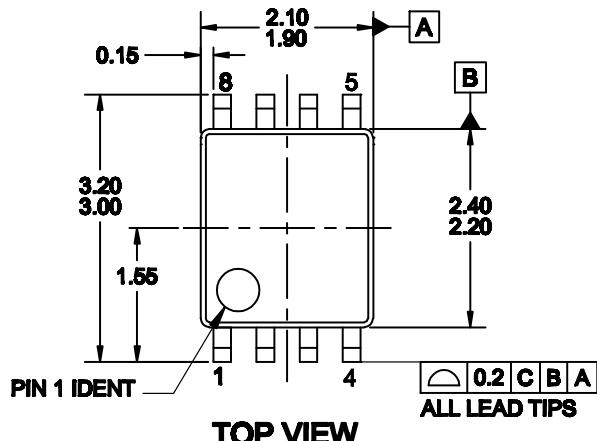
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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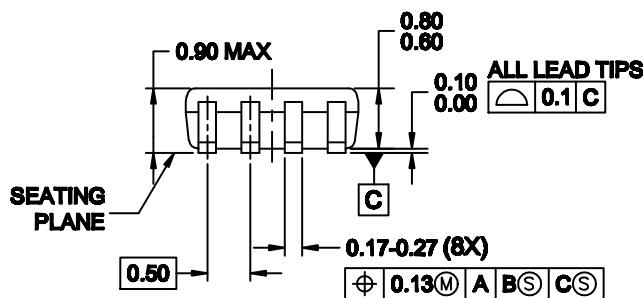
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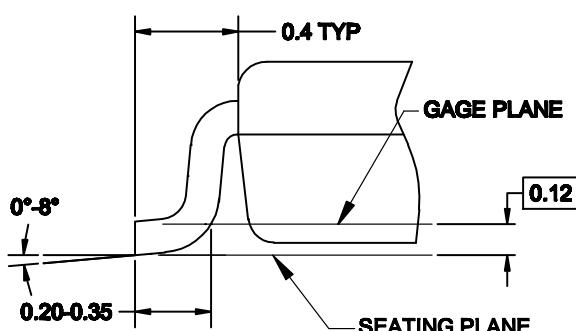
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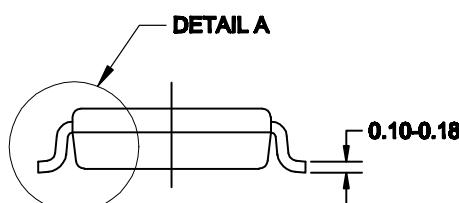
SIDE VIEW



DETAIL A

NOTES:

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